

RS16xxHxF Series 16A TRIACS

DESCRIPTION:

High current density due to double mesa technology, glass passivation, guaranteed maximum junction temperature 150° C.

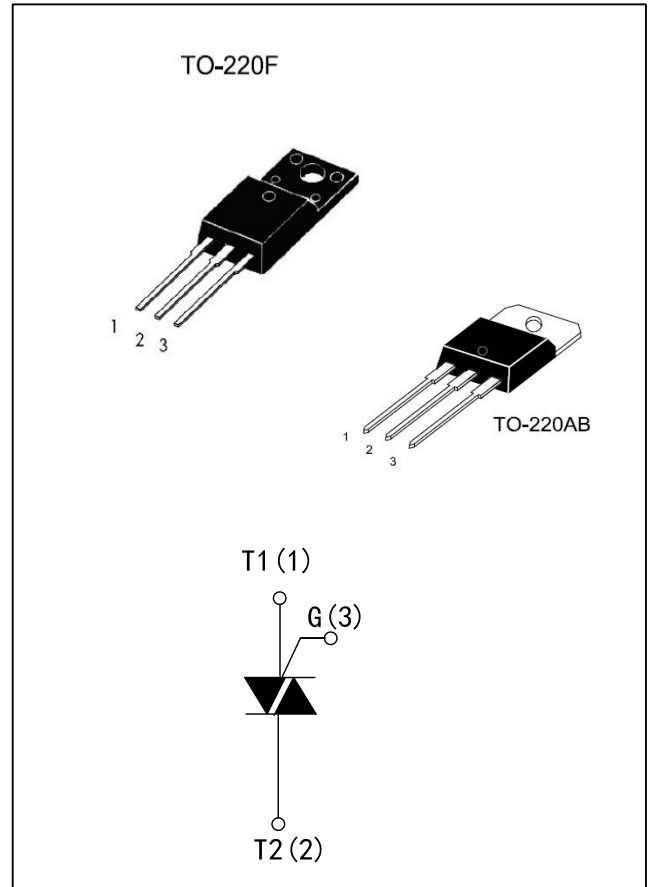
RS16xxH series triacs are suitable for general purpose AC switching, They can be used as an ON/OFF function in applications such as static relays, washing machine, soymlk maker, flush toilet, hair drier, induction motor staing circuits...or for phase contol operation light dimmers, motor speed controllers.

RS1610H-1620H-1635H-1650H are 3 quadrants triacs, They are specially recommended for use on inductive loads.

RS16xxHxF series are full pack plastic e, they provide a 2000V RMS isolation voltage from all three terminals to external heat sink.

MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	16	A
V_{DRM}/V_{RRM}	600 and 800	V
V_{TM}	≤ 1.55	V



ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		Tstg	-40 to +150	°C
Operating junction temperature range		Tj	-40 to +150	°C
Repetitive Peak Off-state Voltage	Tj=25°C	VDRM	600and800	V
Repetitive Peak Reverse Voltage	Tj=25°C	VRRM	600and800	
Non repetitive Surge Peak Off-state Voltage	tp=10ms, Tj=25°C	VDSM	700and900	V
Non repetitive Peak Reverse Voltage		VRSM	700and900	
RMS on-state current (full sine wave)		IT(RMS)	16	A
Non repetitive surge peak on-state current (full cycle, Tj=25°C)	f = 60 Hz t=16.7ms	ITSM	168	A
	f = 50 Hz t=20ms		160	
I²t Value for fusing		I²t	144	A²s
Critical rate of rise of on-state current IG=2×IGT, tr≤100 ns, f=120Hz, Tj=150°C		di /dt	50	A/μs
Peak gate current	tp=20us, Tj=150°C	IGM	4	A
Peak gate power	tp=20us, Tj=150°C	PGM	5	W
Average gate power dissipation Tj=150°C		PG(AV)	1	W

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ\text{C}$ unless otherwise specified)

Symbol	Test Condition	Quadrant		Limits				Unit
				RS1610H	RS1620H	RS1635H	RS1650H	
I_{GT}	$V_D=12\text{V}$ $R_L=33\Omega$	I-II-III	MAX.	10	20	35	50	mA
V_{GT}		I-II-III	MAX.	1.5				V
V_{GD}	$V_D=V_{DRM}$ $R_L=3.3\text{K}\Omega$ $T_j=150^\circ\text{C}$	I-II-III	MIN.	0.2				V
I_L	$I_G=1.2I_{GT}$	I-III	MAX.	20	40	50	70	mA
		II	MAX.	35	55	70	100	mA
I_H	$I_T=100\text{mA}$		MAX.	20	30	45	60	mA
dV/dt	$V_D=67\%V_{DRM}$ gate open $T_j=150^\circ\text{C}$		MIN.	200	500	1000	1500	V/ μs
$(dV/dt)_c$	$V_D=400\text{V}$ $(dI/dt)_c=-7\text{A/ms}$ $T_j=150^\circ\text{C}$		MIN.	1	5	15	20	V/ μs

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=22.5\text{A}$, $t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	1.55	V
I_{DRM} I_{RRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25^\circ\text{C}$	10	μA
		$T_j=150^\circ\text{C}$	4.0	mA

THERMAL RESISTANCES

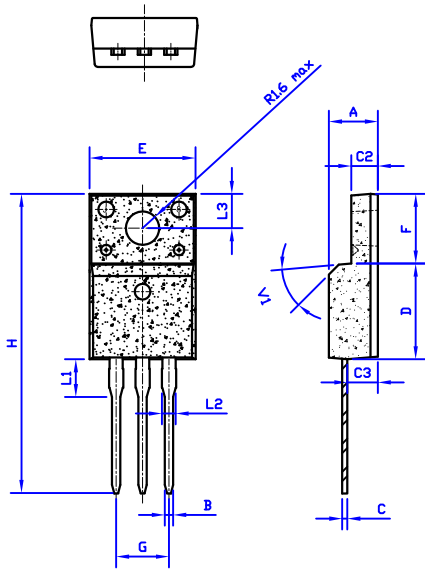
Symbol	Parameter		Value	Unit
$R_{th(J-C)}$	Junction to Case(AC)	TO-220F	3.0	$^\circ\text{C/W}$

ORDERING INFORMATION

R S 16 xx H x F
SIKA CO., LIMITED TRIAC SERIES $I_{T(RMS)}: 16\text{A}$
10: $I_{GT123} \leq 10\text{mA}$ 20: $I_{GT123} \leq 20\text{mA}$ 35: $I_{GT123} \leq 35\text{mA}$ 50: $I_{GT123} \leq 50\text{mA}$
F: TO-220F A: TO-220A B: TO-220B E: D ² PAK 6: $V_{DRM}/V_{RRM} \geq 600\text{V}$ 8: $V_{DRM}/V_{RRM} \geq 800\text{V}$ High junction temperature

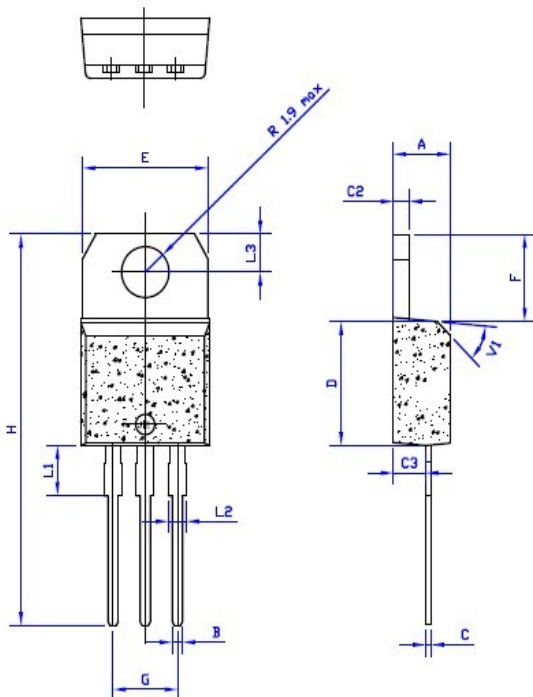
PACKAGE MECHANICAL DATA

TO-220F



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.4		4.8	0.173		0.189
B	0.74	0.8	0.83	0.029	0.031	0.033
C	0.5		0.75	0.020		0.030
C2	2.4		2.7	0.094		0.106
C3	2.6		3.0	0.102		0.118
D	8.8		9.3	0.346		0.367
E	9.7		10.3	0.382		0.406
F	6.4		6.8	0.252		0.268
G	5.0		5.2	0.197		0.205
H	28.0		29.8	11.0		11.7
L1		3.63			0.143	
L2	1.14		1.7	0.044		0.067
L3		3.3			0.130	
V1		40°			40°	

TO-220A insulated package and TO-220B non-insulated package



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.4		4.6	0.173		1.181
B	0.61		0.88	0.024		0.034
C	0.46		0.70	0.018		0.027
C2	1.23		1.32	0.048		0.051
C3	2.4		2.72	0.094		0.107
D	8.6		9.7	0.338		0.382
E	9.8		10.4	0.386		0.409
F	6.2		6.6	0.244		0.259
G	4.8		5.4	0.189		0.213
H	28.0		29.8	11.0		11.7
L1		3.75			0.147	
L2	1.14		1.7	0.044		0.066
L3	2.65		2.95	0.104		0.116
V1		40°			40°	

FIG.1:Maximum power dissipation versus RMS on-state current(full cycle)

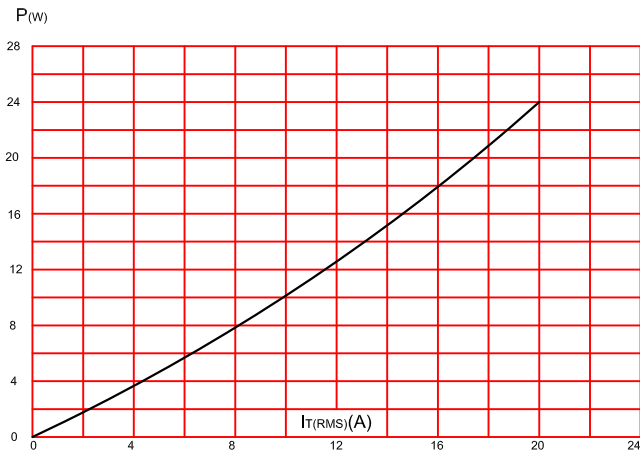


FIG.2:RMS on-state current versus case temperature(full cycle)

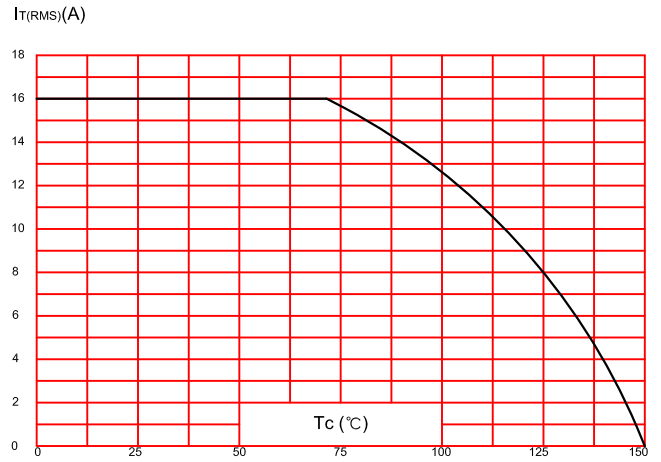


FIG.3:On-state characteristics (maximum values).

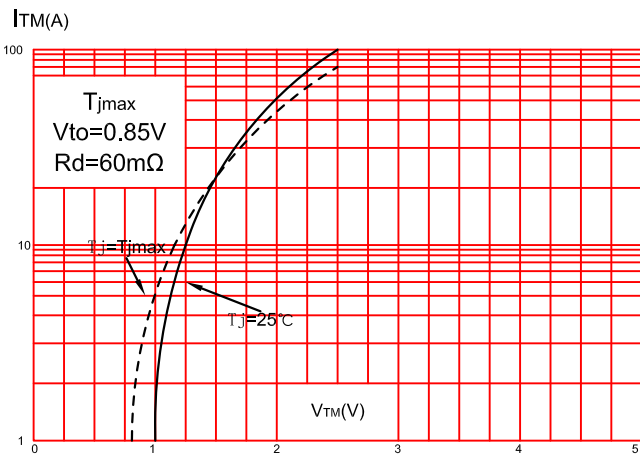


FIG.4:Surge peak on-state current versus number of cycles.

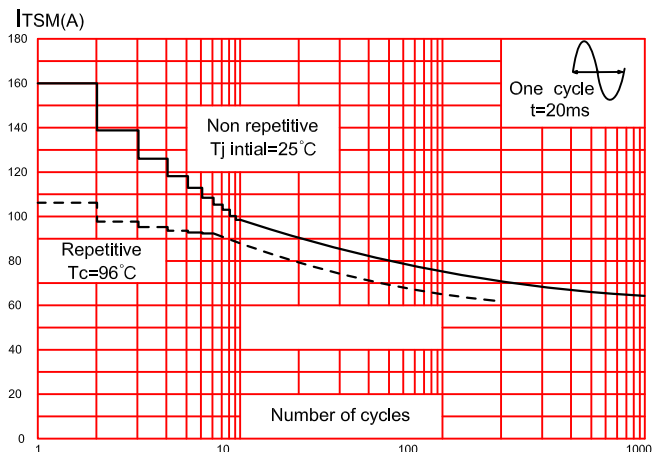


FIG.5:Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$, and corresponding value of I^2t .

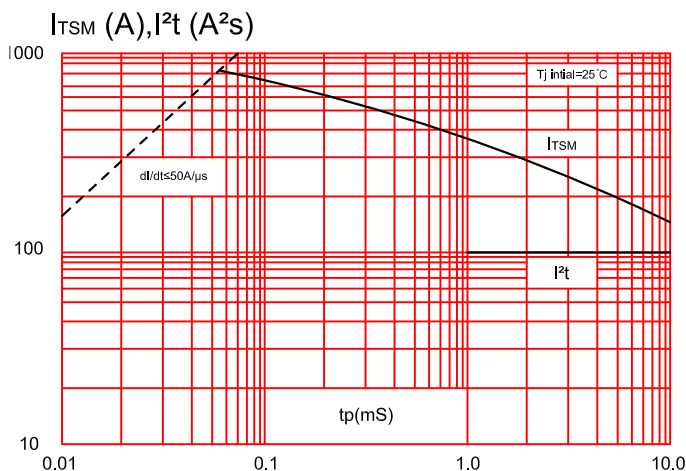


FIG.6:Relative variations of gate trigger current, holding current and latching current versus junction temperature(typical values)

